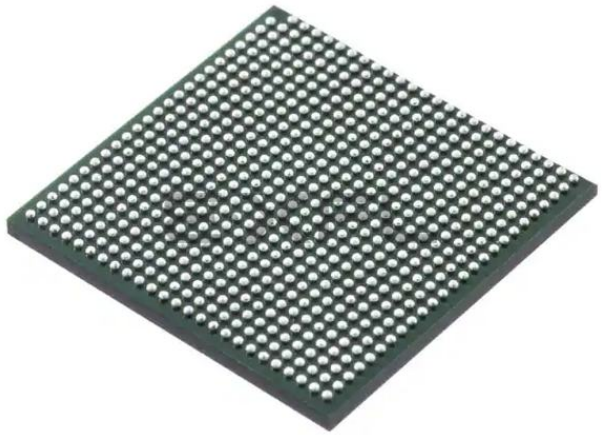

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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	ARM® Cortex®-A9
Number of Cores/Bus Width	2 Core, 32-Bit
Speed	1.0GHz
Co-Processors/DSP	Multimedia; NEON™ SIMD
RAM Controllers	LPDDR2, LVDDR3, DDR3
Graphics Acceleration	Yes
Display & Interface Controllers	Keypad, LCD
Ethernet	10/100/1000Mbps (1)
SATA	SATA 3Gbps (1)
USB	USB 2.0 + PHY (4)
Voltage - I/O	1.8V, 2.5V, 2.8V, 3.3V
Operating Temperature	-40°C ~ 125°C (TJ)
Security Features	ARM TZ, Boot Security, Cryptography, RTIC, Secure Fusebox, Secure JTAG, Secure Memory, Secure RTC, Tamper Detection
Package / Case	624-FBGA, FCBGA
Supplier Device Package	624-FCBGA (21x21)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/mcimx6d6avt10aer

- Two Master AXI (64-bit) bus interfaces output of L2 cache
- Frequency of the core (including Neon and L1 cache) as per Table 6.
- NEON MPE coprocessor
  - SIMD Media Processing Architecture
  - NEON register file with 32x64-bit general-purpose registers
  - NEON Integer execute pipeline (ALU, Shift, MAC)
  - NEON dual, single-precision floating point execute pipeline (FADD, FMUL)
  - NEON load/store and permute pipeline

The SoC-level memory system consists of the following additional components:

- Boot ROM, including HAB (96 KB)
- Internal multimedia / shared, fast access RAM (OCRAM, 256 KB)
- Secure/non-secure RAM (16 KB)
- External memory interfaces:
  - 16-bit, 32-bit, and 64-bit DDR3-1066, DDR3L-1066, and 1/2 LPDDR2-800 channels, supporting DDR interleaving mode, for dual x32 LPDDR2
  - 8-bit NAND-Flash, including support for Raw MLC/SLC, 2 KB, 4 KB, and 8 KB page size, BA-NAND, PBA-NAND, LBA-NAND, OneNAND™ and others. BCH ECC up to 40 bit.
  - 16/32-bit NOR Flash. All EIMv2 pins are muxed on other interfaces.
  - 16/32-bit PSRAM, Cellular RAM

Each i.MX 6Dual/6Quad processor enables the following interfaces to external devices (some of them are muxed and not available simultaneously):

- Hard Disk Drives—SATA II, 3.0 Gbps
- Displays—Total five interfaces available. Total raw pixel rate of all interfaces is up to 450 Mpixels/sec, 24 bpp. Up to four interfaces may be active in parallel.
  - One Parallel 24-bit display port, up to 225 Mpixels/sec (for example, WUXGA at 60 Hz or dual HD1080 and WXGA at 60 Hz)
  - LVDS serial ports—One port up to 170 Mpixels/sec (for example, WUXGA at 60 Hz) or two ports up to 85 MP/sec each
  - HDMI 1.4 port
  - MIPI/DSI, two lanes at 1 Gbps
- Camera sensors:
  - Parallel Camera port (up to 20 bit and up to 240 MHz peak)
  - MIPI CSI-2 serial camera port, supporting up to 1000 Mbps/lane in 1/2/3-lane mode and up to 800 Mbps/lane in 4-lane mode. The CSI-2 Receiver core can manage one clock lane and up to four data lanes. Each i.MX 6Dual/6Quad processor has four lanes.
- Expansion cards:
  - Four MMC/SD/SDIO card ports all supporting:

Table 6. Operating Ranges (continued)

Parameter Description	Symbol	Min	Typ	Max[1]	Unit	Comment[2]
GPIO supplies[10]	NVCC_CSI, NVCC_EIM0, NVCC_EIM1, NVCC_EIM2, NVCC_ENET, NVCC_GPIO, NVCC_LCD, NVCC_NANDF, NVCC_SD1, NVCC_SD2, NVCC_SD3, NVCC_JTAG	1.65	1.8, 2.8, 3.3	3.6	V	Isolation between the NVCC_EIMx and NVCC_SDx different supplies allow them to operate at different voltages within the specified range. Example: NVCC_EIM1 can operate at 1.8 V while NVCC_EIM2 operates at 3.3 V.
	NVCC_LVDS_2P5[11] NVCC_MIPI	2.25	2.5	2.75	V	—
HDMI supply voltages	HDMI_VP	0.99	1.1	1.3	V	—
	HDMI_VPH	2.25	2.5	2.75	V	—
PCIe supply voltages	PCIE_VP	1.023	1.1	1.3	V	—
	PCIE_VPH	2.325	2.5	2.75	V	—
	PCIE_VPTX	1.023	1.1	1.3	V	—
SATA Supply voltages	SATA_VP	0.99	1.1	1.3	V	—
	SATA_VPH	2.25	2.5	2.75	V	—
Junction temperature	T_J	-40	95	125	°C	See *i.MX 6Dual/6Quad Product Lifetime Usage Estimates Application Note*, AN4724, for information on product lifetime (power-on years) for this processor.

1 Applying the maximum voltage results in maximum power consumption and heat generation. NXP recommends a voltage set point = (Vmin + the supply tolerance). This results in an optimized power/speed ratio.

2 See the *Hardware Development Guide for i.MX 6Quad, 6Dual, 6DualLite, 6Solo Families of Applications Processors* (IMX6DQ6SDLHDG) for bypass capacitors requirements for each of the *_CAP supply outputs.

3 For Quad core system, connect to VDD_ARM_IN. For Dual core system, may be shorted to GND together with VDD_ARM23_CAP to reduce leakage.

4 VDD_ARM_IN and VDD_SOC_IN must be at least 125 mV higher than the LDO Output Set Point for correct voltage regulation.

5 VDD_ARM_CAP must not exceed VDD_CACHE_CAP by more than +50 mV. VDD_CACHE_CAP must not exceed VDD_ARM_CAP by more than 200 mV.

6 VDD_SOC_CAP and VDD_PU_CAP must be equal.

7 In LDO enabled mode, the internal LDO output set points must be configured such that the:

VDD_ARM LDO output set point does not exceed the VDD_SOC LDO output set point by more than 100 mV.

VDD_SOC LDO output set point is equal to the VDD_PU LDO output set point.

The VDD_ARM LDO output set point can be lower than the VDD_SOC LDO output set point, however, the minimum output set points shown in this table must be maintained.

8 In LDO bypassed mode, the external power supply must ensure that VDD_ARM_IN does not exceed VDD_SOC_IN by more than 100 mV. The VDD_ARM_IN supply voltage can be lower than the VDD_SOC_IN supply voltage. The minimum voltages shown in this table must be maintained.

9 To set VDD_SNVS_IN voltage with respect to Charging Currents and RTC, see the *Hardware Development Guide for i.MX 6Dual, 6Quad, 6Solo, 6DualLite Families of Applications Processors* (IMX6DQ6SDLHDG).

Table 9. Stop Mode Current and Power Consumption (continued)

Mode	Test Conditions	Supply	Typical[1]	Unit
STOP_ON	• ARM LDO set to 0.9 V • SoC and PU LDOs set to 1.225 V • HIGH LDO set to 2.5 V • PLLs disabled • DDR is in self refresh	VDD_ARM_IN (1.4 V)	7.5	mA
		VDD_SOC_IN (1.4 V)	22	mA
		VDD_HIGH_IN (3.0 V)	3.7	mA
		Total	52	mW
STOP_OFF	• ARM LDO set to 0.9 V • SoC LDO set to 1.225 V • PU LDO is power gated • HIGH LDO set to 2.5 V • PLLs disabled • DDR is in self refresh	VDD_ARM_IN (1.4 V)	7.5	mA
		VDD_SOC_IN (1.4 V)	13.5	mA
		VDD_HIGH_IN (3.0 V)	3.7	mA
		Total	41	mW
STANDBY	• ARM and PU LDOs are power gated • SoC LDO is in bypass • HIGH LDO is set to 2.5 V • PLLs are disabled • Low voltage • Well Bias ON • Crystal oscillator is enabled	VDD_ARM_IN (0.9 V)	0.1	mA
		VDD_SOC_IN (0.9 V)	13	mA
		VDD_HIGH_IN (3.0 V)	3.7	mA
		Total	22	mW
Deep Sleep Mode (DSM)	• ARM and PU LDOs are power gated • SoC LDO is in bypass • HIGH LDO is set to 2.5 V • PLLs are disabled • Low voltage • Well Bias ON • Crystal oscillator and bandgap are disabled	VDD_ARM_IN (0.9 V)	0.1	mA
		VDD_SOC_IN (0.9 V)	2	mA
		VDD_HIGH_IN (3.0 V)	0.5	mA
		Total	3.4	mW
SNVS Only	• VDD_SNVS_IN powered • All other supplies off • SRTC running	VDD_SNVS_IN (2.8V)	41	µA
		Total	115	µW

[1] The typical values shown here are for information only and are not guaranteed. These values are average values measured on a worst-case wafer at 25°C.

CAUTION

The internal RTC oscillator does not provide an accurate frequency and is affected by process, voltage, and temperature variations. NXP strongly recommends using an external crystal as the RTC_XTALI reference. If the internal oscillator is used instead, careful consideration must be given to the timing implications on all of the SoC modules dependent on this clock.

The OSC32k runs from VDD_SNVS_CAP, which comes from the VDD_HIGH_IN/VDD_SNVS_IN power mux.

Table 20. OSC32K Main Characteristics

Parameter	Min	Typ	Max	Comments
Fosc	—	32.768 kHz	—	This frequency is nominal and determined mainly by the crystal selected. 32.0 K would work as well.
Current consumption	—	4 μA	—	The typical value shown is only for the oscillator, driven by an external crystal. If the internal ring oscillator is used instead of an external crystal, then approximately 25 μA must be added to this value.
Bias resistor	—	14 MΩ	—	This the integrated bias resistor that sets the amplifier into a high gain state. Any leakage through the ESD network, external board leakage, or even a scope probe that is significant relative to this value will debias the amplifier. The debiasing will result in low gain, and will impact the circuit's ability to start up and maintain oscillations.
Target Crystal Properties				
Cload	—	10 pF	—	Usually crystals can be purchased tuned for different Cloads. This Cload value is typically 1/2 of the capacitances realized on the PCB on either side of the quartz. A higher Cload will decrease oscillation margin, but increases current oscillating through the crystal.
ESR	—	50 kΩ	100 kΩ	Equivalent series resistance of the crystal. Choosing a crystal with a higher value will decrease the oscillating margin.

4.6 I/O DC Parameters

This section includes the DC parameters of the following I/O types:

- General Purpose I/O (GPIO)
- Double Data Rate I/O (DDR) for LPDDR2 and DDR3/DDR3L modes
- LVDS I/O
- MLB I/O

NOTE

The term ‘OVDD’ in this section refers to the associated supply rail of an input or output.

Table 23. RGMII I/O 2.5V I/O DC Electrical Parameters[1]

Parameter	Symbol	Test Conditions	Min	Max	Units
High-level output voltage[1]	V_{OH}	Ioh= -0.1 mA (DSE=001,010) Ioh= -1.0 mA (DSE=011,100,101,110,111)	OVDD-0.15	—	V
Low-level output voltage[1]	V_{OL}	Iol= 0.1 mA (DSE=001,010) Iol= 1.0 mA (DSE=011,100,101,110,111)	—	0.15	V
Input Reference Voltage	V_{ref}	—	0.49xOVDD	0.51xOVDD	V
High-Level input voltage [2, 3]	V_{IH}	—	0.7xOVDD	OVDD	V
Low-Level input voltage [2, 3]	V_{IL}	—	0	0.3xOVDD	V
Input Hysteresis(OVDD=1.8V)	$V_{HYS\_HighVDD}$	OVDD=1.8V	250	—	mV
Input Hysteresis(OVDD=2.5V)	$V_{HYS\_HighVDD}$	OVDD=2.5V	250	—	mV
Schmitt trigger VT+ [3, 4]	V_{TH+}	—	0.5xOVDD	—	mV
Schmitt trigger VT- [3, 4]	V_{TH-}	—	—	0.5xOVDD	mV
Pull-up resistor (22 kΩ PU)	R_{PU_22K}	V_{in}=0V	—	212	µA
Pull-up resistor (22 kΩ PU)	R_{PU_22K}	V_{in}=OVDD	—	1	µA
Pull-up resistor (47 kΩ PU)	R_{PU_47K}	V_{in}=0V	—	100	µA
Pull-up resistor (47 kΩ PU)	R_{PU_47K}	V_{in}=OVDD	—	1	µA
Pull-up resistor (100 kΩ PU)	R_{PU_100K}	V_{in}=0V	—	48	µA
Pull-up resistor (100 kΩ PU)	R_{PU_100K}	V_{in}=OVDD	—	1	µA
Pull-down resistor (100 kΩ PD)	R_{PD_100K}	V_{in}=OVDD	—	48	µA
Pull-down resistor (100 kΩ PD)	R_{PD_100K}	V_{in}=0V	—	1	µA
Keeper Circuit Resistance	R_{keep}	—	105	165	kΩ
Input current (no pull-up/down)	I_{in}	V_I = 0,VI = OVDD	-2.9	2.9	µA

1 Input Mode Selection: SW_PAD_CTL_GRP_DDR_TYPE_RGMII = 10 (1.8V Mode)
SW_PAD_CTL_GRP_DDR_TYPE_RGMII = 11 (2.5V Mode)

2 Overshoot and undershoot conditions (transitions above OVDD and below GND) on switching pads must be held below 0.6 V, and the duration of the overshoot/undershoot must not exceed 10% of the system clock cycle. Overshoot/ undershoot must be controlled through printed circuit board layout, transmission line impedance matching, signal line termination, or other methods. Non-compliance to this specification may affect device reliability or cause permanent damage to the device.

3 To maintain a valid level, the transition edge of the input must sustain a constant slew rate (monotonic) from the current DC level through to the target DC level, Vil or Vih. Monotonic input transition time is from 0.1 ns to 1 s.

4 Hysteresis of 250 mV is guaranteed over all operating conditions when hysteresis is enabled (register IOMUXC_SW_PAD_CTL_PAD_RGMII_TXC[HYS]= 0).

4.6.4.1 LPDDR2 Mode I/O DC Parameters

For details on supported DDR memory configurations, see Section 4.10.2, "MMDC Supported DDR3/DDR3L/LPDDR2 Configurations."

The parameters in Table 24 are guaranteed per the operating ranges in Table 6, unless otherwise noted.

Table 25. DDR3/DDR3L I/O DC Electrical Parameters (continued)

Parameters	Symbol	Test Conditions	Min	Max	Unit
Termination Voltage	Vtt	Vtt tracking OVDD/2	0.49 × OVDD	0.51 × OVDD	V
Input current (no pull-up/down)	Iin	Vin = 0 or OVDD	-2.9	2.9	μA
Pull-up/pull-down impedance mismatch	MMpupd	—	-10	10	%
240 Ω unit calibration resolution	Rres	—	—	10	Ω
Keeper circuit resistance	Rkeep	—	105	175	kΩ

1 OVDD – I/O power supply (1.425 V–1.575 V for DDR3 and 1.283 V–1.45 V for DDR3L).

2 Vref – DDR3/DDR3L external reference voltage.

3 The single-ended signals need to be within the respective limits (Vih(dc) max, Vil(dc) min) for single-ended signals as well as the limitations for overshoot and undershoot (see Table 31).

4.6.5 LVDS I/O DC Parameters

The LVDS interface complies with TIA/EIA 644-A standard. See TIA/EIA STANDARD 644-A, "*Electrical Characteristics of Low Voltage Differential Signaling (LVDS) Interface Circuits*" for details.

Table 26 shows the Low Voltage Differential Signalling (LVDS) I/O DC parameters.

Table 26. LVDS I/O DC Parameters

Parameter	Symbol	Test Conditions	Min	Max	Unit
Output Differential Voltage	V_{OD}	Rload=100 Ω between padP and padN	250	450	mV
Output High Voltage	V_{OH}	I_{OH} = 0 mA	1.25	1.6	V
Output Low Voltage	V_{OL}	I_{OL} = 0 mA	0.9	1.25	
Offset Voltage	V_{OS}	—	1.125	1.375	

4.6.6 MLB 6-Pin I/O DC Parameters

The MLB interface complies with Analog Interface of 6-pin differential Media Local Bus specification version 4.1. See 6-pin differential MLB specification v4.1, "MediaLB 6-pin interface Electrical Characteristics" for details.

NOTE

The MLB 6-pin interface does not support speed mode 8192fs.

Table 27 shows the Media Local Bus (MLB) I/O DC parameters.

4.8.2 DDR I/O Output Buffer Impedance

For details on supported DDR memory configurations, see Section 4.10.2, "MMDC Supported DDR3/DDR3L/LPDDR2 Configurations."

Table 36 shows DDR I/O output buffer impedance of i.MX 6Dual/6Quad processors.

Table 36. DDR I/O Output Buffer Impedance

Parameter	Symbol	Test Conditions	Typical		Unit
			NVCC_DRAM=1.5 V (DDR3) DDR_SEL=11	NVCC_DRAM=1.2 V (LPDDR2) DDR_SEL=10	
Output Driver Impedance	Rdrv	Drive Strength (DSE) = 000 001 010 011 100 101 110 111	 Hi-Z 240 120 80 60 48 40 34	 Hi-Z 240 120 80 60 48 40 34	Ω

Note:

1. Output driver impedance is controlled across PVTs using ZQ calibration procedure.
2. Calibration is done against 240 W external reference resistor.
3. Output driver impedance deviation (calibration accuracy) is ±5% (max/min impedance) across PVTs.

4.8.3 LVDS I/O Output Buffer Impedance

The LVDS interface complies with TIA/EIA 644-A standard. See, TIA/EIA STANDARD 644-A, "Electrical Characteristics of Low Voltage Differential Signaling (LVDS) Interface Circuits" for details.

4.8.4 MLB 6-Pin I/O Differential Output Impedance

Table 37 shows MLB 6-pin I/O differential output impedance of i.MX 6Dual/6Quad processors.

Table 37. MLB 6-Pin I/O Differential Output Impedance

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Differential Output Impedance	Z_O	—	1.6	—	—	kΩ

Table 42. EIM Asynchronous Timing Parameters Relative to Chip Select[1, 2] (continued)

Ref No.	Parameter	Determination by Synchronous measured parameters	Min	Max	Unit
WE40	EIM_LBA_B Invalid to EIM_CSx_B Invalid (ADVL is asserted)	WE7-WE15-CSN×t	-3.5-CSN×t	3.5-CSN×t	ns
WE40A (muxed A/D)	EIM_CSx_B Valid to EIM_LBA_B Invalid	WE14-WE6+(ADVN+ADVA+1-CSA)×t	-3.5+(ADVN+ADVA+1-CSA)×t	3.5+(ADVN+ADVA+1-CSA)×t	ns
WE41	EIM_CSx_B Valid to Output Data Valid	WE16-WE6-WCSA×t	-3.5-WCSA×t	3.5-WCSA×t	ns
WE41A (muxed A/D)	EIM_CSx_B Valid to Output Data Valid	WE16-WE6+(WADVN+WADVA+ADH+1-WCSA)×t	-3.5+(WADVN+WADVA+ADH+1-WCSA)×t	3.5+(WADVN+WADVA+ADH+1-WCSA)×t	ns
WE42	Output Data Invalid to EIM_CSx_B Invalid	WE17-WE7-CSN×t	-3.5-CSN×t	3.5-CSN×t	ns
MAXCO	Output maximum delay from internal driving EIM_ADDRxx/control flip-flops to chip outputs.	10	—	10	ns
MAXCSO	Output maximum delay from internal chip selects driving flip-flops to EIM_CSx_B out.	10	—	10	ns
MAXDI	EIM_DATAxx MAXIMUM delay from chip input data to its internal flip-flop	5	—	5	ns
WE43	Input Data Valid to EIM_CSx_B Invalid	MAXCO-MAXCSO+MAXDI	MAXCO-MAXCSO+MAXDI	—	ns
WE44	EIM_CSx_B Invalid to Input Data Invalid	0	0	—	ns
WE45	EIM_CSx_B Valid to EIM_EBx_B Valid (Write access)	WE12-WE6+(WBEA-WCSA)×t	-3.5+(WBEA-WCSA)×t	3.5+(WBEA-WCSA)×t	ns
WE46	EIM_EBx_B Invalid to EIM_CSx_B Invalid (Write access)	WE7-WE13+(WBEN-WCSN)×t	-3.5+(WBEN-WCSN)×t	3.5+(WBEN-WCSN)×t	ns
MAXDTI	Maximum delay from EIM_DTACK_B input to its internal flip-flop + 2 cycles for synchronization	10	—	10	ns
WE47	EIM_DTACK_B Active to EIM_CSx_B Invalid	MAXCO-MAXCSO+MAXDTI	MAXCO-MAXCSO+MAXDTI	—	ns
WE48	EIM_CSx_B Invalid to EIM_DTACK_B invalid	0	0	—	ns

1 For more information on configuration parameters mentioned in this table, see the i.MX 6Dual/6Quad reference manual (IMX6DQRM).

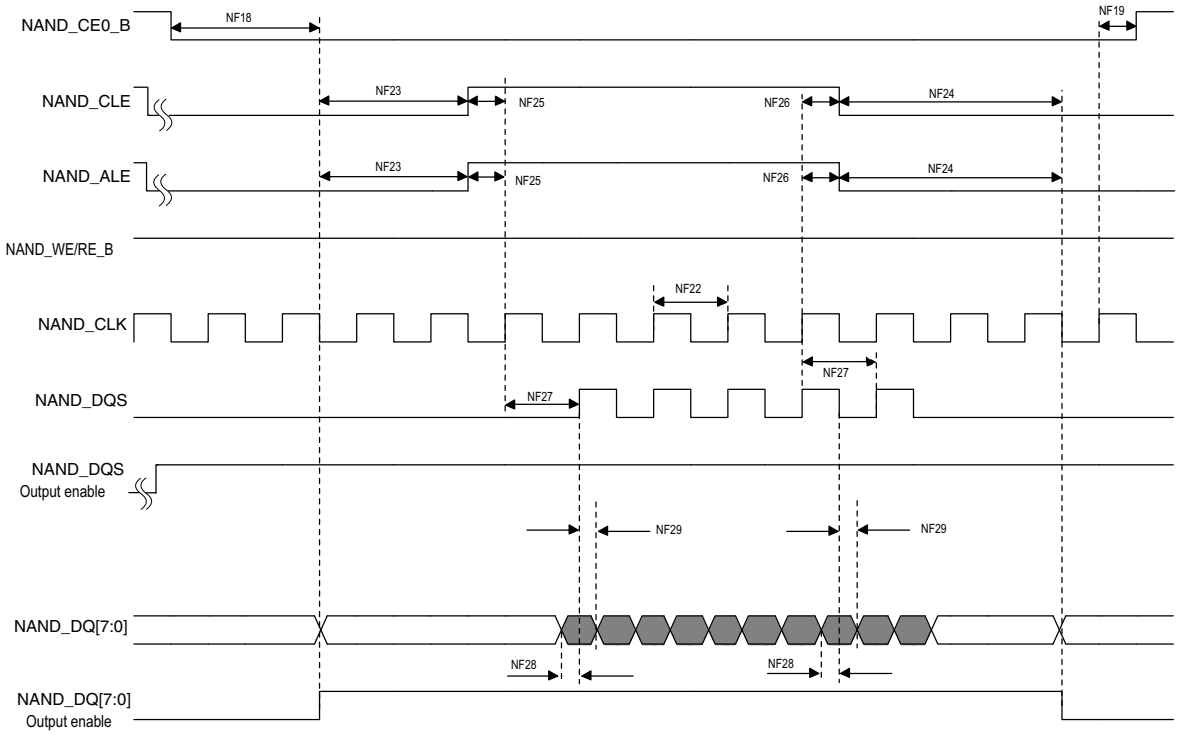

Figure 30. Source Synchronous Mode Data Write Timing Diagram

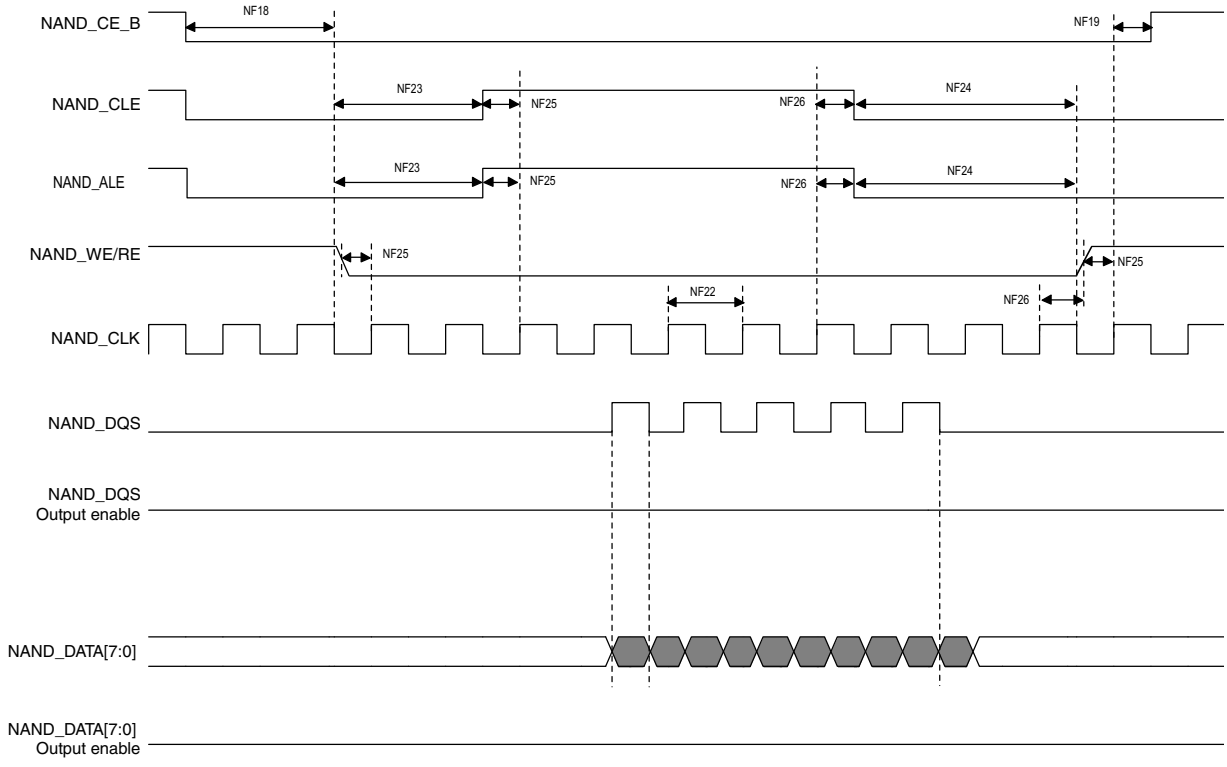

Figure 31. Source Synchronous Mode Data Read Timing Diagram

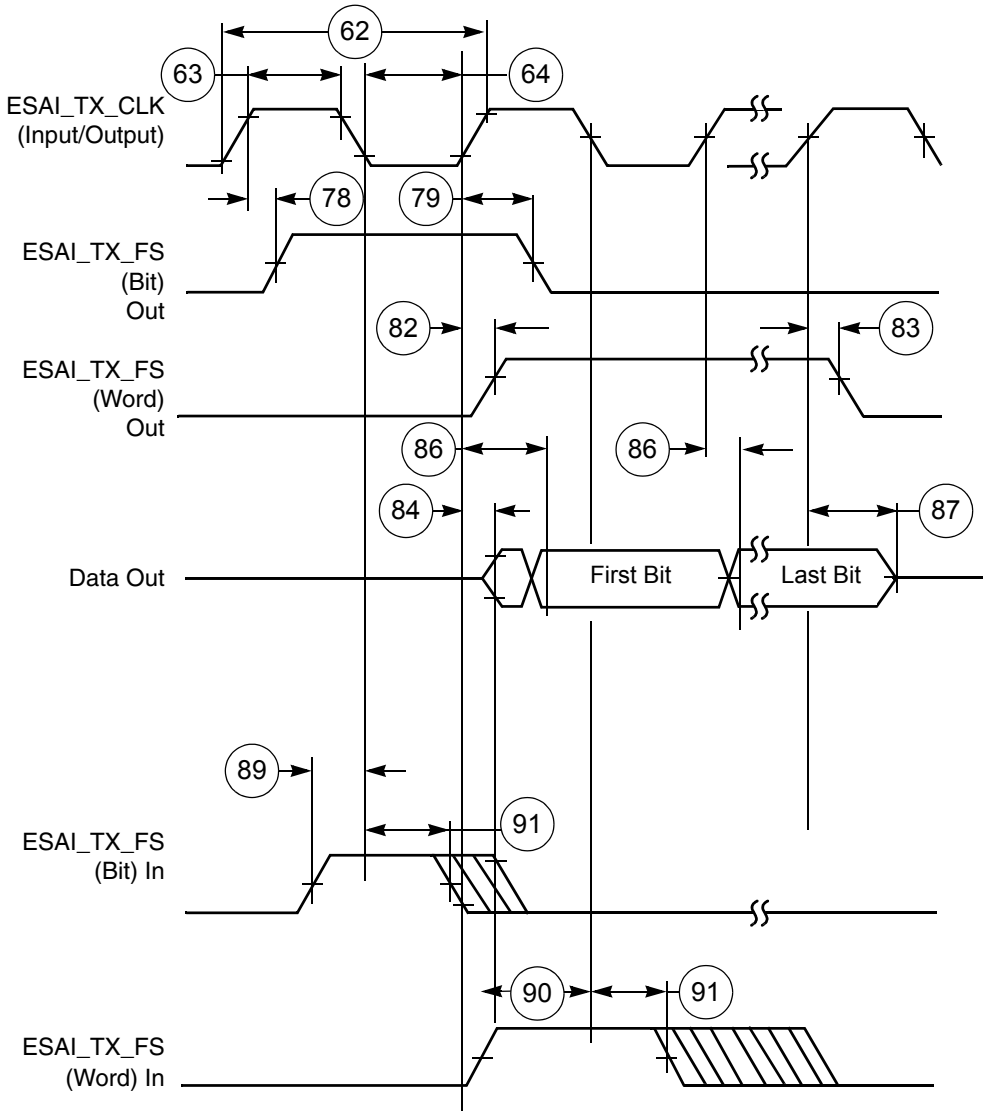

Figure 37. ESAI Transmitter Timing

Table 50. SD/eMMC4.3 Interface Timing Specification (continued)

ID	Parameter	Symbols	Min	Max	Unit
eSDHC Input/Card Outputs SD_CMD, SD_DATAx (Reference to SDx_CLK)					
SD7	eSDHC Input Setup Time	t_{ISU}	2.5	—	ns
SD8	eSDHC Input Hold Time[4]	t_{IH}	1.5	—	ns

1 In low speed mode, card clock must be lower than 400 kHz, voltage ranges from 2.7 to 3.6 V.

2 In normal (full) speed mode for SD/SDIO card, clock frequency can be any value between 0—25 MHz. In high-speed mode, clock frequency can be any value between 0—50 MHz.

3 In normal (full) speed mode for MMC card, clock frequency can be any value between 0—20 MHz. In high-speed mode, clock frequency can be any value between 0—52 MHz.

4 To satisfy hold timing, the delay difference between clock input and cmd/data input must not exceed 2 ns.

4.12.4.2 eMMC4.4/4.41 (Dual Data Rate) eSDHCv3 AC Timing

Figure 40 depicts the timing of eMMC4.4/4.41. Table 51 lists the eMMC4.4/4.41 timing characteristics. Be aware that only SDx_DATAx is sampled on both edges of the clock (not applicable to SD_CMD).

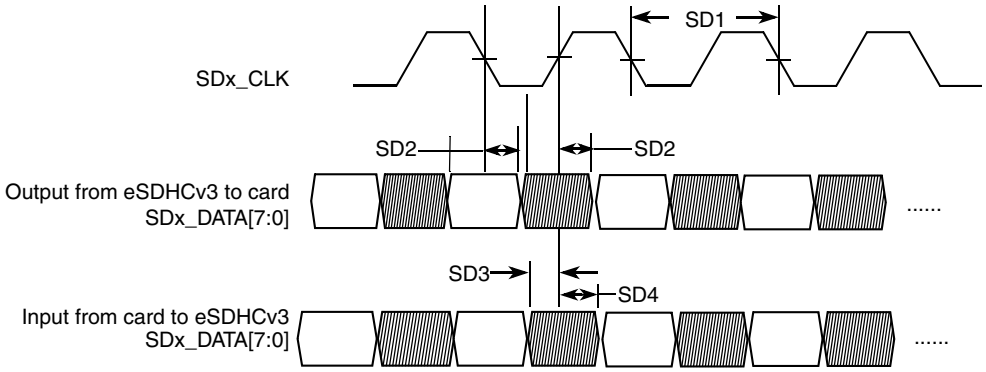

Figure 40. eMMC4.4/4.41 Timing

Table 51. eMMC4.4/4.41 Interface Timing Specification

ID	Parameter	Symbols	Min	Max	Unit
Card Input Clock[1]					
SD1	Clock Frequency (EMMC4.4 DDR)	f_{PP}	0	52	MHz
SD1	Clock Frequency (SD3.0 DDR)	f_{PP}	0	50	MHz
uSDHC Output / Card Inputs SD_CMD, SD_DATAx (Reference to SD_CLK)					
SD2	uSDHC Output Delay	t_{OD}	2.5	7.1	ns
uSDHC Input / Card Outputs SD_CMD, SD_DATAx (Reference to SD_CLK)					
SD3	uSDHC Input Setup Time	t_{ISU}	1.7	—	ns
SD4	uSDHC Input Hold Time	t_{IH}	1.5	—	ns

1 Clock duty cycle will be in the range of 47% to 53%.

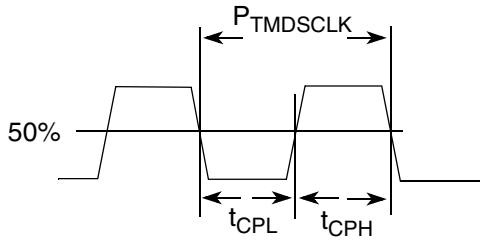

Figure 53. TMDS Clock Signal Definitions

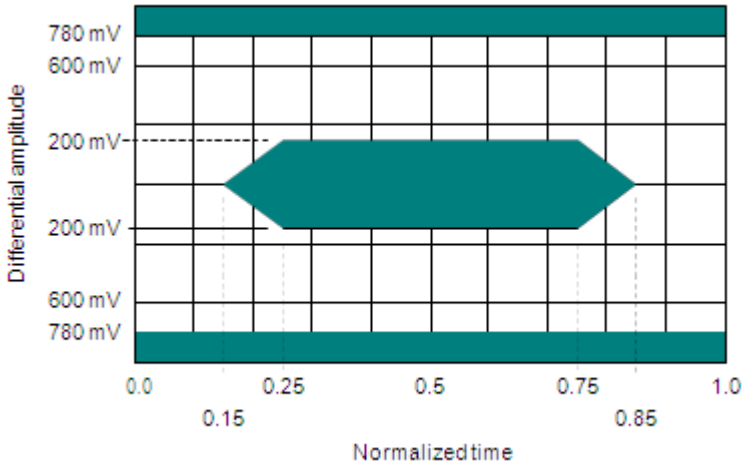

Figure 54. Eye Diagram Mask Definition for HDMI Driver Signal Specification at TP1

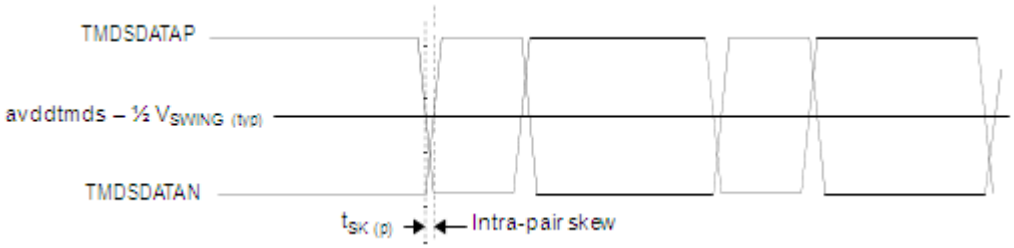

Figure 55. Intra-Pair Skew Definition

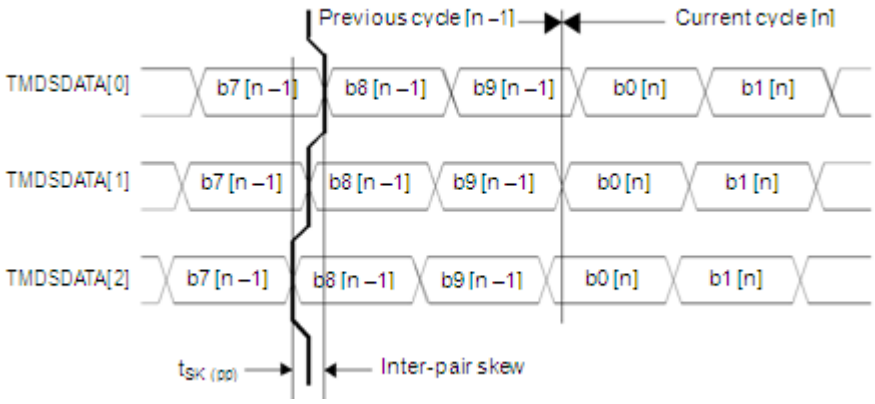

Figure 56. Inter-Pair Skew Definition

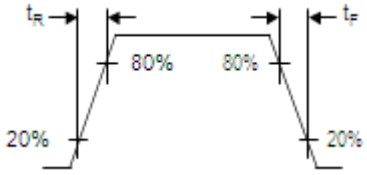

Figure 57. TMDS Output Signals Rise and Fall Time Definition

Table 60. Switching Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TMDS Drivers Specifications						
—	Maximum serial data rate	—	—	—	3.4	Gbps
$F_{TMDSCLK}$	TMDSCLK frequency	On TMDSCLKP/N outputs	25	—	340	MHz
$P_{TMDSCLK}$	TMDSCLK period	RL = 50 Ω See Figure 53.	2.94	—	40	ns
t_{CDC}	TMDSCLK duty cycle	$t_{CDC} = t_{CPH} / P_{TMDSCLK}$ RL = 50 Ω See Figure 53.	40	50	60	%
t_{CPH}	TMDSCLK high time	RL = 50 Ω See Figure 53.	4	5	6	UI
t_{CPL}	TMDSCLK low time	RL = 50 Ω See Figure 53.	4	5	6	UI
—	TMDSCLK jitter[1]	RL = 50 Ω	—	—	0.25	UI
$t_{SK(p)}$	Intra-pair (pulse) skew	RL = 50 Ω See Figure 55.	—	—	0.15	UI
$t_{SK(pp)}$	Inter-pair skew	RL = 50 Ω See Figure 56.	—	—	1	UI
t_R	Differential output signal rise time	20–80% RL = 50 Ω See Figure 57.	75	—	0.4 UI	ps

There are special physical outputs to provide synchronous controls:

- The ipp_disp_clk is a dedicated base synchronous signal that is used to generate a base display (component, pixel) clock for a display.
- The ipp_pin_1– ipp_pin_7 are general purpose synchronous pins, that can be used to provide HSYNC, VSYNC, DRDY or any else independent signal to a display.

The IPU has a system of internal binding counters for internal events (such as, HSYNC/VSYNC) calculation. The internal event (local start point) is synchronized with internal DI_CLK. A suitable control starts from the local start point with predefined UP and DOWN values to calculate control's changing points with half DI_CLK resolution. A full description of the counter system can be found in the IPU chapter of the i.MX 6Dual/6Quad reference manual (IMX6DQRM).

4.12.10.5.2 Asynchronous Controls

The asynchronous control is a data-oriented signal that changes its value with an output data according to additional internal flags coming with the data.

There are special physical outputs to provide asynchronous controls, as follows:

- The ipp_d0_cs and ipp_d1_cs pins are dedicated to provide chip select signals to two displays.
- The ipp_pin_11– ipp_pin_17 are general purpose asynchronous pins, that can be used to provide WR. RD, RS or any other data-oriented signal to display.

NOTE

The IPU has independent signal generators for asynchronous signals toggling. When a DI decides to put a new asynchronous data on the bus, a new internal start (local start point) is generated. The signal generators calculate predefined UP and DOWN values to change pins states with half DI_CLK resolution.

4.12.10.6 Synchronous Interfaces to Standard Active Matrix TFT LCD Panels

4.12.10.6.1 IPU Display Operating Signals

The IPU uses four control signals and data to operate a standard synchronous interface:

- IPP_DISP_CLK—Clock to display
- HSYNC—Horizontal synchronization
- VSYNC—Vertical synchronization
- DRDY—Active data

All synchronous display controls are generated on the base of an internally generated "local start point". The synchronous display controls can be placed on time axis with DI's offset, up and down parameters. The display access can be whole number of DI clock (Tdiclk) only. The IPP_DATA can not be moved relative to the local start point. The data bus of the synchronous interface is output direction only.

Table 69. Electrical and Timing Information (continued)

Symbol	Parameters	Test Conditions	Min	Typ	Max	Unit
L_S	Equivalent wire bond series inductance	—	—	—	1.5	nH
R_S	Equivalent wire bond series resistance	—	—	—	0.15	Ω
R_L	Load Resistance	—	80	100	125	Ω

4.12.12.6 High-Speed Clock Timing

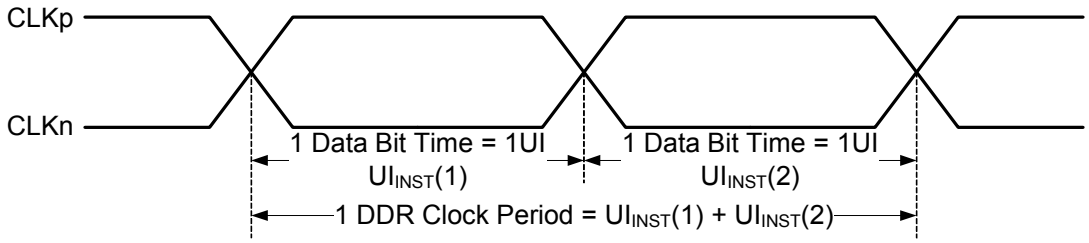

Figure 69. DDR Clock Definition

4.12.12.7 Forward High-Speed Data Transmission Timing

The timing relationship of the DDR Clock differential signal to the Data differential signal is shown in Figure 70:

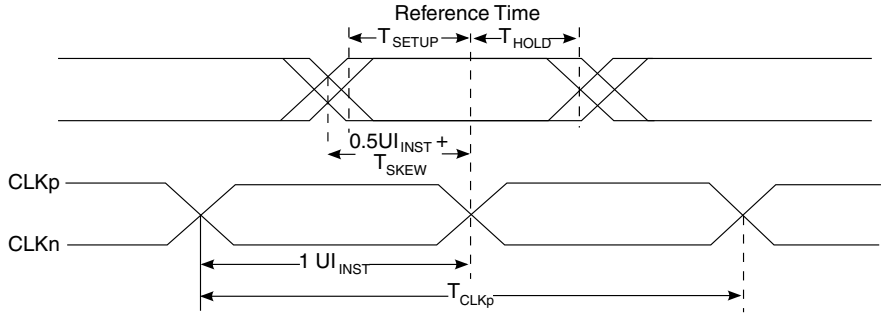

Figure 70. Data to Clock Timing Definitions

4.12.12.8 Reverse High-Speed Data Transmission Timing

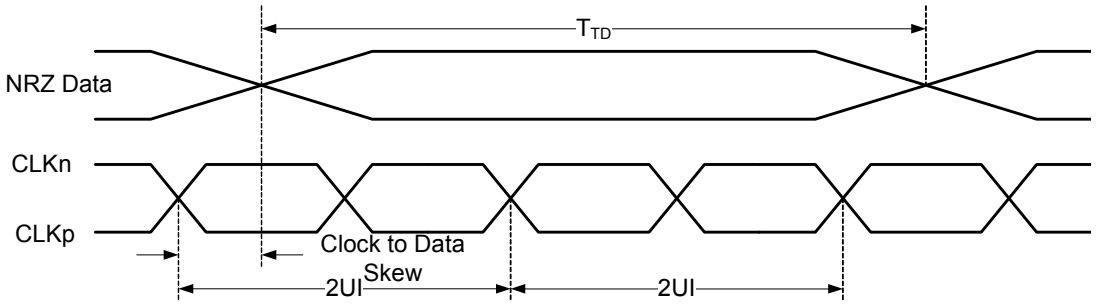

Figure 71. Reverse High-Speed Data Transmission Timing at Slave Side

4.12.15.1 PCIE_REXT Reference Resistor Connection

The impedance calibration process requires connection of reference resistor 200 Ω. 1% precision resistor on PCIE_REXT pads to ground. It is used for termination impedance calibration.

4.12.16 Pulse Width Modulator (PWM) Timing Parameters

This section describes the electrical information of the PWM. The PWM can be programmed to select one of three clock signals as its source frequency. The selected clock signal is passed through a prescaler before being input to the counter. The output is available at the pulse-width modulator output (PWMO) external pin.

Figure 83 depicts the timing of the PWM, and Table 76 lists the PWM timing parameters.

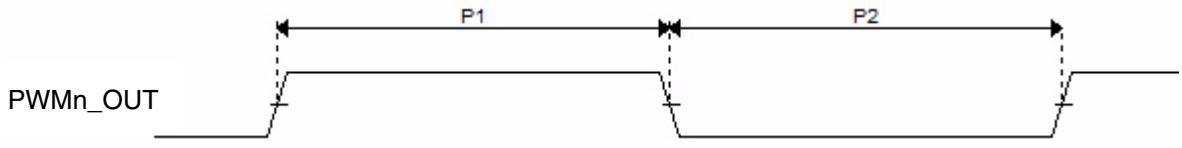

Figure 83. PWM Timing

Table 76. PWM Output Timing Parameters

ID	Parameter	Min	Max	Unit
—	PWM Module Clock Frequency	0	ipg_clk	MHz
P1	PWM output pulse width high	15	—	ns
P2	PWM output pulse width low	15	—	ns

4.12.17 SATA PHY Parameters

This section describes SATA PHY electrical specifications.

4.12.17.1 Transmitter and Receiver Characteristics

The SATA PHY meets or exceeds the electrical compliance requirements defined in the SATA specifications.

NOTE

The tables in the following sections indicate any exceptions to the SATA specification or aspects of the SATA PHY that exceed the standard, as well as provide information about parameters not defined in the standard.

The following subsections provide values obtained from a combination of simulations and silicon characterization.

4.12.21.2 UART RS-232 Serial Mode Timing

The following sections describe the electrical information of the UART module in the RS-232 mode.

4.12.21.2.1 UART Transmitter

Figure 94 depicts the transmit timing of UART in the RS-232 serial mode, with 8 data bit/1 stop bit format. Table 87 lists the UART RS-232 serial mode transmit timing characteristics.

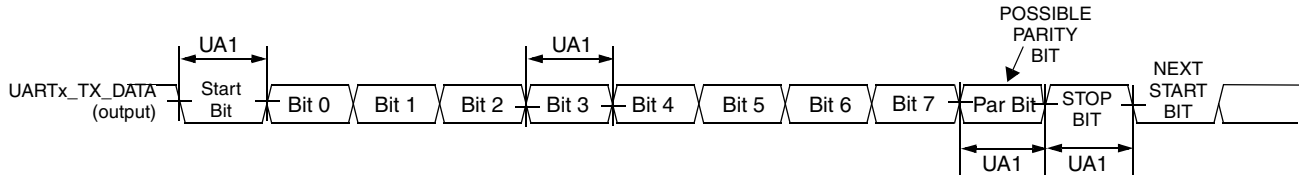

Figure 94. UART RS-232 Serial Mode Transmit Timing Diagram

Table 87. RS-232 Serial Mode Transmit Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA1	Transmit Bit Time	t_{Tbit}	$1/F_{baud\_rate}$ [1] – T_{ref_clk} [2]	$1/F_{baud\_rate} + T_{ref\_clk}$	—

[1] F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

[2] T_{ref_clk}: The period of UART reference clock *ref_clk* (*ipg_perclk* after RFDIV divider).

4.12.21.2.2 UART Receiver

Figure 95 depicts the RS-232 serial mode receive timing with 8 data bit/1 stop bit format. Table 88 lists serial mode receive timing characteristics.

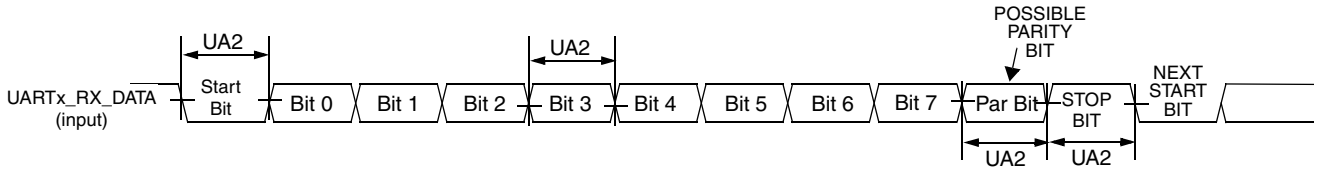

Figure 95. UART RS-232 Serial Mode Receive Timing Diagram

Table 88. RS-232 Serial Mode Receive Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA2	Receive Bit Time[1]	t_{Rbit}	$1/F_{baud\_rate}$ [2] – $1/(16 \times F_{baud\_rate})$	$1/F_{baud\_rate} + 1/(16 \times F_{baud\_rate})$	—

[1] The UART receiver can tolerate $1/(16 \times F_{baud\_rate})$ tolerance in each bit. But accumulation tolerance in one frame must not exceed $3/(16 \times F_{baud\_rate})$.

[2] F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

4.12.21.2.3 UART IrDA Mode Timing

The following subsections give the UART transmit and receive timings in IrDA mode.

UART IrDA Mode Transmitter

Figure 96 depicts the UART IrDA mode transmit timing, with 8 data bit/1 stop bit format. Table 89 lists the transmit timing characteristics.

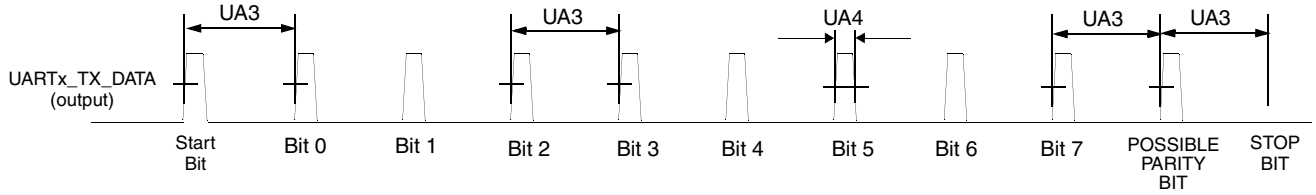

Figure 96. UART IrDA Mode Transmit Timing Diagram

Table 89. IrDA Mode Transmit Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA3	Transmit Bit Time in IrDA mode	t_{TIRbit}	$1/F_{baud\_rate}$ [1] – T_{ref_clk} [2]	$1/F_{baud\_rate} + T_{ref\_clk}$	—
UA4	Transmit IR Pulse Duration	$t_{TIRpulse}$	$(3/16) \times (1/F_{baud\_rate}) - T_{ref\_clk}$	$(3/16) \times (1/F_{baud\_rate}) + T_{ref\_clk}$	—

1 F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

2 T_{ref_clk}: The period of UART reference clock *ref_clk* (*ipg_perclk* after RFDIV divider).

UART IrDA Mode Receiver

Figure 97 depicts the UART IrDA mode receive timing, with 8 data bit/1 stop bit format. Table 90 lists the receive timing characteristics.

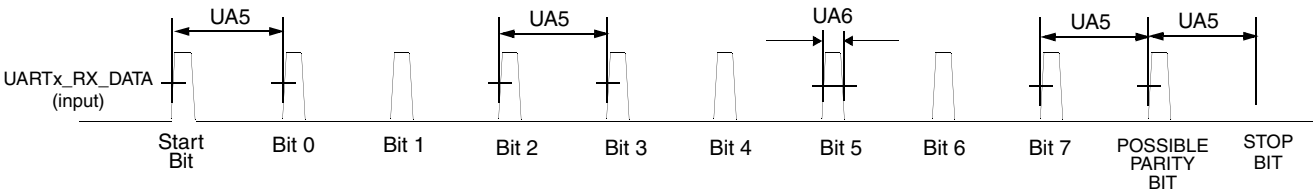

Figure 97. UART IrDA Mode Receive Timing Diagram

Table 90. IrDA Mode Receive Timing Parameters

ID	Parameter	Symbol	Min	Max	Unit
UA5	Receive Bit Time[1] in IrDA mode	t_{RIRbit}	$1/F_{baud\_rate}$ [2] – $1/(16 \times F_{baud\_rate})$	$1/F_{baud\_rate} + 1/(16 \times F_{baud\_rate})$	—
UA6	Receive IR Pulse Duration	$t_{RIRpulse}$	1.41 µs	$(5/16) \times (1/F_{baud\_rate})$	—

1 The UART receiver can tolerate $1/(16 \times F_{baud\_rate})$ tolerance in each bit. But accumulation tolerance in one frame must not exceed $3/(16 \times F_{baud\_rate})$.

2 F_{baud_rate}: Baud rate frequency. The maximum baud rate the UART can support is (*ipg_perclk* frequency)/16.

Table 96. 21 x 21 mm Functional Contact Assignments (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[1]			
				Default Mode (Reset Mode)	Default Function (Signal Name)	Input/Output	Value[2]
CSI_D1P	D2	NVCC_MIPI	—	—	CSI_DATA1_P	—	—
CSI_D2M	E1	NVCC_MIPI	—	—	CSI_DATA2_N	—	—
CSI_D2P	E2	NVCC_MIPI	—	—	CSI_DATA2_P	—	—
CSI_D3M	F2	NVCC_MIPI	—	—	CSI_DATA3_N	—	—
CSI_D3P	F1	NVCC_MIPI	—	—	CSI_DATA3_P	—	—
CSI0_DAT10	M1	NVCC_CSI	GPIO	ALT5	GPIO5_IO28	Input	PU (100K)
CSI0_DAT11	M3	NVCC_CSI	GPIO	ALT5	GPIO5_IO29	Input	PU (100K)
CSI0_DAT12	M2	NVCC_CSI	GPIO	ALT5	GPIO5_IO30	Input	PU (100K)
CSI0_DAT13	L1	NVCC_CSI	GPIO	ALT5	GPIO5_IO31	Input	PU (100K)
CSI0_DAT14	M4	NVCC_CSI	GPIO	ALT5	GPIO6_IO00	Input	PU (100K)
CSI0_DAT15	M5	NVCC_CSI	GPIO	ALT5	GPIO6_IO01	Input	PU (100K)
CSI0_DAT16	L4	NVCC_CSI	GPIO	ALT5	GPIO6_IO02	Input	PU (100K)
CSI0_DAT17	L3	NVCC_CSI	GPIO	ALT5	GPIO6_IO03	Input	PU (100K)
CSI0_DAT18	M6	NVCC_CSI	GPIO	ALT5	GPIO6_IO04	Input	PU (100K)
CSI0_DAT19	L6	NVCC_CSI	GPIO	ALT5	GPIO6_IO05	Input	PU (100K)
CSI0_DAT4	N1	NVCC_CSI	GPIO	ALT5	GPIO5_IO22	Input	PU (100K)
CSI0_DAT5	P2	NVCC_CSI	GPIO	ALT5	GPIO5_IO23	Input	PU (100K)
CSI0_DAT6	N4	NVCC_CSI	GPIO	ALT5	GPIO5_IO24	Input	PU (100K)
CSI0_DAT7	N3	NVCC_CSI	GPIO	ALT5	GPIO5_IO25	Input	PU (100K)
CSI0_DAT8	N6	NVCC_CSI	GPIO	ALT5	GPIO5_IO26	Input	PU (100K)
CSI0_DAT9	N5	NVCC_CSI	GPIO	ALT5	GPIO5_IO27	Input	PU (100K)
CSI0_DATA_EN	P3	NVCC_CSI	GPIO	ALT5	GPIO5_IO20	Input	PU (100K)
CSI0_MCLK	P4	NVCC_CSI	GPIO	ALT5	GPIO5_IO19	Input	PU (100K)
CSI0_PIXCLK	P1	NVCC_CSI	GPIO	ALT5	GPIO5_IO18	Input	PU (100K)
CSI0_VSYNC	N2	NVCC_CSI	GPIO	ALT5	GPIO5_IO21	Input	PU (100K)
DI0_DISP_CLK	N19	NVCC_LCD	GPIO	ALT5	GPIO4_IO16	Input	PU (100K)
DI0_PIN15	N21	NVCC_LCD	GPIO	ALT5	GPIO4_IO17	Input	PU (100K)
DI0_PIN2	N25	NVCC_LCD	GPIO	ALT5	GPIO4_IO18	Input	PU (100K)
DI0_PIN3	N20	NVCC_LCD	GPIO	ALT5	GPIO4_IO19	Input	PU (100K)
DI0_PIN4	P25	NVCC_LCD	GPIO	ALT5	GPIO4_IO20	Input	PU (100K)
DISP0_DAT0	P24	NVCC_LCD	GPIO	ALT5	GPIO4_IO21	Input	PU (100K)
DISP0_DAT1	P22	NVCC_LCD	GPIO	ALT5	GPIO4_IO22	Input	PU (100K)
DISP0_DAT10	R21	NVCC_LCD	GPIO	ALT5	GPIO4_IO31	Input	PU (100K)
DISP0_DAT11	T23	NVCC_LCD	GPIO	ALT5	GPIO5_IO05	Input	PU (100K)
DISP0_DAT12	T24	NVCC_LCD	GPIO	ALT5	GPIO5_IO06	Input	PU (100K)
DISP0_DAT13	R20	NVCC_LCD	GPIO	ALT5	GPIO5_IO07	Input	PU (100K)

Table 96. 21 x 21 mm Functional Contact Assignments (continued)

Ball Name	Ball	Power Group	Ball Type	Out of Reset Condition[1]			
				Default Mode (Reset Mode)	Default Function (Signal Name)	Input/Output	Value[2]
DRAM_CS1	AD17	NVCC_DRAM	DDR	ALT0	DRAM_CS1_B	Output	0
DRAM_D0	AD2	NVCC_DRAM	DDR	ALT0	DRAM_DATA00	Input	PU (100K)
DRAM_D1	AE2	NVCC_DRAM	DDR	ALT0	DRAM_DATA01	Input	PU (100K)
DRAM_D10	AA6	NVCC_DRAM	DDR	ALT0	DRAM_DATA10	Input	PU (100K)
DRAM_D11	AE7	NVCC_DRAM	DDR	ALT0	DRAM_DATA11	Input	PU (100K)
DRAM_D12	AB5	NVCC_DRAM	DDR	ALT0	DRAM_DATA12	Input	PU (100K)
DRAM_D13	AC5	NVCC_DRAM	DDR	ALT0	DRAM_DATA13	Input	PU (100K)
DRAM_D14	AB6	NVCC_DRAM	DDR	ALT0	DRAM_DATA14	Input	PU (100K)
DRAM_D15	AC7	NVCC_DRAM	DDR	ALT0	DRAM_DATA15	Input	PU (100K)
DRAM_D16	AB7	NVCC_DRAM	DDR	ALT0	DRAM_DATA16	Input	PU (100K)
DRAM_D17	AA8	NVCC_DRAM	DDR	ALT0	DRAM_DATA17	Input	PU (100K)
DRAM_D18	AB9	NVCC_DRAM	DDR	ALT0	DRAM_DATA18	Input	PU (100K)
DRAM_D19	Y9	NVCC_DRAM	DDR	ALT0	DRAM_DATA19	Input	PU (100K)
DRAM_D2	AC4	NVCC_DRAM	DDR	ALT0	DRAM_DATA02	Input	PU (100K)
DRAM_D20	Y7	NVCC_DRAM	DDR	ALT0	DRAM_DATA20	Input	PU (100K)
DRAM_D21	Y8	NVCC_DRAM	DDR	ALT0	DRAM_DATA21	Input	PU (100K)
DRAM_D22	AC8	NVCC_DRAM	DDR	ALT0	DRAM_DATA22	Input	PU (100K)
DRAM_D23	AA9	NVCC_DRAM	DDR	ALT0	DRAM_DATA23	Input	PU (100K)
DRAM_D24	AE9	NVCC_DRAM	DDR	ALT0	DRAM_DATA24	Input	PU (100K)
DRAM_D25	Y10	NVCC_DRAM	DDR	ALT0	DRAM_DATA25	Input	PU (100K)
DRAM_D26	AE11	NVCC_DRAM	DDR	ALT0	DRAM_DATA26	Input	PU (100K)
DRAM_D27	AB11	NVCC_DRAM	DDR	ALT0	DRAM_DATA27	Input	PU (100K)
DRAM_D28	AC9	NVCC_DRAM	DDR	ALT0	DRAM_DATA28	Input	PU (100K)
DRAM_D29	AD9	NVCC_DRAM	DDR	ALT0	DRAM_DATA29	Input	PU (100K)
DRAM_D3	AA5	NVCC_DRAM	DDR	ALT0	DRAM_DATA03	Input	PU (100K)
DRAM_D30	AD11	NVCC_DRAM	DDR	ALT0	DRAM_DATA30	Input	PU (100K)
DRAM_D31	AC11	NVCC_DRAM	DDR	ALT0	DRAM_DATA31	Input	PU (100K)
DRAM_D32	AA17	NVCC_DRAM	DDR	ALT0	DRAM_DATA32	Input	PU (100K)
DRAM_D33	AA18	NVCC_DRAM	DDR	ALT0	DRAM_DATA33	Input	PU (100K)
DRAM_D34	AC18	NVCC_DRAM	DDR	ALT0	DRAM_DATA34	Input	PU (100K)
DRAM_D35	AE19	NVCC_DRAM	DDR	ALT0	DRAM_DATA35	Input	PU (100K)
DRAM_D36	Y17	NVCC_DRAM	DDR	ALT0	DRAM_DATA36	Input	PU (100K)
DRAM_D37	Y18	NVCC_DRAM	DDR	ALT0	DRAM_DATA37	Input	PU (100K)
DRAM_D38	AB19	NVCC_DRAM	DDR	ALT0	DRAM_DATA38	Input	PU (100K)
DRAM_D39	AC19	NVCC_DRAM	DDR	ALT0	DRAM_DATA39	Input	PU (100K)
DRAM_D4	AC1	NVCC_DRAM	DDR	ALT0	DRAM_DATA04	Input	PU (100K)